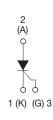
VS-12TTS08PbF, VS-12TTS08-M3

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High Voltage Phase Control Thyristor, 12 A

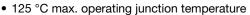


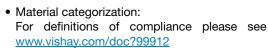


PRODUCT SUMMARY				
Package	TO-220AB			
Diode variation	Single SCR			
I _{T(AV)}	8 A			
V _{DRM} /V _{RRM}	800 V			
V_{TM}	1.2 V			
I _{GT}	15 mA			
T _J	- 40 °C to 125 °C			

FEATURES











ROHS COMPLIANT HALOGEN FREE Available

APPLICATIONS

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge.

DESCRIPTION

The VS-12TTS08... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS					
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS					
Capacitive input filter T _A = 55 °C, T _J = 125 °C, common heatsink of 1 °C/W	13.5	17	А		

MAJOR RATINGS AND CHARACTERISTICS				
PARAMETER	RAMETER TEST CONDITIONS VALUES		UNITS	
I _{T(AV)}	Sinusoidal waveform	8	٨	
I _{T(RMS)}		12.5	A	
V _{DRM} /V _{RRM}		800	V	
I _{TSM}		110	A	
V _T	8 A, T _J = 25 °C	1.2	V	
dV/dt		150	V/µs	
dl/dt		100	A/μs	
T _J	Range	- 40 to 125	°C	

VOLTAGE RATINGS					
PART NUMBER	V _{RRM} , MAXIMUM PEAK VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA		
VS-12TTS08PbF, VS-12TTS08-M3	800	800	1.0		



VS-12TTS08PbF, VS-12TTS08-M3

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PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum average on-state current	I _{T(AV)}	T 100 °C 100° conduction half sine ways	8	
Maximum RMS on-state current	I _{T(RMS)}	T _C = 108 °C, 180° conduction, half sine wave	12.5	
Maximum peak, one-cycle,	,	10 ms sine pulse, rated V _{RRM} applied, T _J = 125 °C	95	Α
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no voltage reapplied, T _J = 125 °C	110	
Maximum 12t for fucing	l ² t	10 ms sine pulse, rated V _{RRM} applied, T _J = 125 °C	45	A ² s
Maximum I ² t for fusing	1-1	10 ms sine pulse, no voltage reapplied, T _J = 125 °C		A-s
Maximum I ² √t for fusing	I ² √t	$t = 0.1$ ms to 10 ms, no voltage reapplied, $T_J = 125$ °C	640	A ² √s
Maximum on-state voltage drop	V _{TM}	8 A, T _J = 25 °C	1.2	V
On-state slope resistance	r _t	T 105 °C	16.2	mΩ
Threshold voltage	V _{T(TO)}	T _J = 125 °C	0.87	V
Maximum reverse and direct leakage	1 /1	T _J = 25 °C	0.05	
current	I _{RM} /I _{DM}	$\frac{V_{R} = \text{Rated V}_{RRM}/V_{DRM}}{V_{R} = \text{Rated V}_{RRM}/V_{DRM}}$	1.0	
Typical holding current	I _H	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C	30	mA
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T _J = 25 °C	50	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to } 80 ^{\circ}\text{C, } V_{DRM} = R_g ^{-}\text{k} = \text{Open}$	150	V/µs
Maximum rate of rise of turned-on current	dl/dt		100	A/µs

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P_{GM}		8.0	W	
Maximum average gate power	P _{G(AV)}		2.0	VV	
Maximum peak positive gate current	+ I _{GM}		1.5	Α	
Maximum peak negative gate voltage	- V _{GM}		10	V	
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, T _J = - 65 °C	20		
		Anode supply = 6 V, resistive load, T _J = 25 °C	15	mA	
119901		Anode supply = 6 V, resistive load, T _J = 125 °C	10		
	V _{GT}	Anode supply = 6 V, resistive load, T _J = - 65 °C	1.2	.,,	
Maximum required DC gate voltage to trigger		Anode supply = 6 V, resistive load, T _J = 25 °C	1		
		Anode supply = 6 V, resistive load, T _J = 125 °C	0.7	V	
Maximum DC gate voltage not to trigger	V_{GD}	I _J = 125 °C, V _{DRM} = Rated value			
Maximum DC gate current not to trigger	I _{GD}			mA	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t _{gt}	T _J = 25 °C	0.8	
Typical reverse recovery time	t _{rr}	T _ 105 °C	3	μs
Typical turn-off time	t _q	T _J = 125 °C	100	



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THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		T _J , T _{Stg}		- 40 to 125	°C
Maximum thermal resistance, junction to case		R _{thJC}	DC operation	1.5	
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	OZ.
Mounting torque —	minimum			6 (5)	kgf · cm
	maximum			12 (10)	(lbf · in)
Marking device			Case style TO-220AB	12TT	TS08

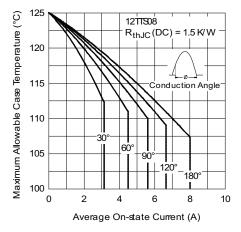


Fig. 1 - Current Ratings Characteristics

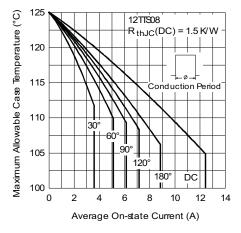


Fig. 2 - Current Ratings Characteristics

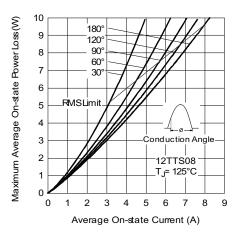


Fig. 3 - On-State Power Loss Characteristics

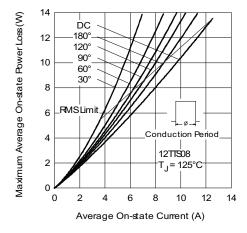


Fig. 4 - On-State Power Loss Characteristics

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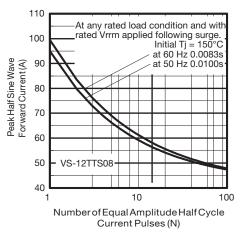


Fig. 5 - Maximum Non-Repetitive Surge Current

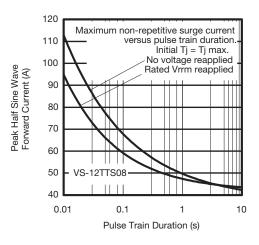


Fig. 6 - Maximum Non-Repetitive Surge Current

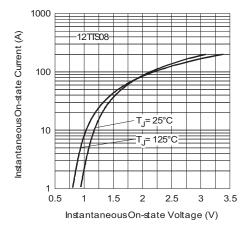


Fig. 7 - On-State Voltage Drop Characteristics

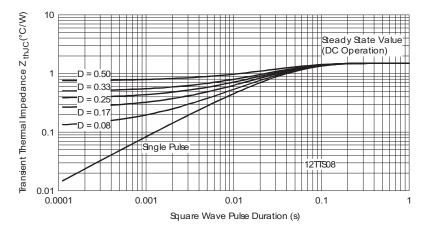


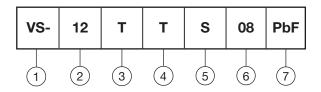
Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

VS-12TTS08PbF, VS-12TTS08-M3

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

Current ratings (12 = 12.5 A)

3 - Circuit configuration:

T = Single thyristor

4 - Package:

T = TO-220

5 - Type of silicon

S = Standard recovery rectifier

6 - Voltage rating (08 = 800 V)

PbF = Lead (Pb)-free and RoHS compliant

-M3 = Halogen-free, RoHS compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)				
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION	
VS-12TTS08PbF	50	1000	Antistatic plastic tubes	
VS-12TTS08-M3	50	1000	Antistatic plastic tubes	

LINKS TO RELATED DOCUMENTS				
Dimensions		www.vishay.com/doc?95222		
Dort marking information	TO-220AB PbF	www.vishay.com/doc?95225		
Part marking information	TO-220AB -M3	www.vishay.com/doc?95028		



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